



SHENZHEN TUOFENG SEMICONDUCTOR TECHNOLOGY CO.,LTD

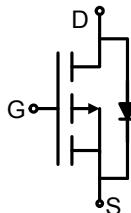
PDFN 5x6 Plastic-Encapsulate MOSFETS

TF3508

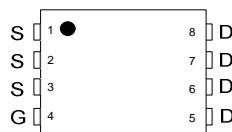
P-Channel Enhancement Mode Power MOSFET

Description

The TF3508 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.



Schematic diagram



Pin assignment



PDFN5x6-8 top view

Application

- Battery Switch
- Load switch
- Power management

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J=150^\circ\text{C}$)	I_D	-60	A
		-35	
Drain Current-Pulsed ^(Note 1)	I_{DM}	-200	A
Maximum Power Dissipation	P_D	40	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	30	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-20\text{A}$	-	6.6	8.0	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-15\text{A}$	-	10	15	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-20\text{A}$	10	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	2900	-	PF
Output Capacitance	C_{oss}		-	410	-	PF
Reverse Transfer Capacitance	C_{rss}		-	280	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-20\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$	-	15	-	nS
Turn-on Rise Time	t_r		-	11	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	44	-	nS
Turn-Off Fall Time	t_f		-	21	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-20\text{A}$ $V_{\text{GS}}=-10\text{V}$	-	48	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	24	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-20\text{A}$	-	0.88	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

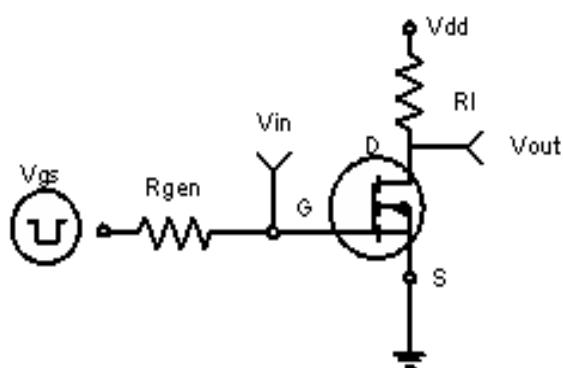


Figure 1 Switching Test Circuit

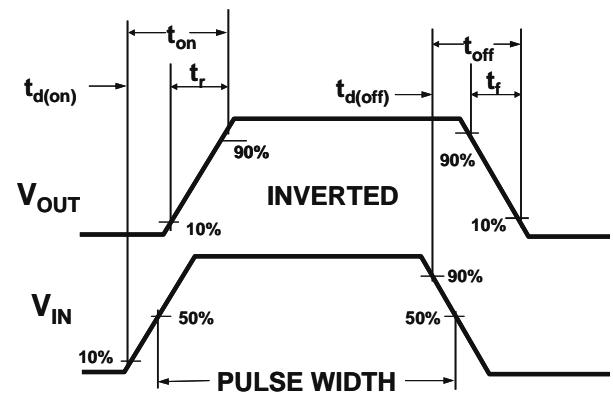


Figure 2 Switching Waveforms

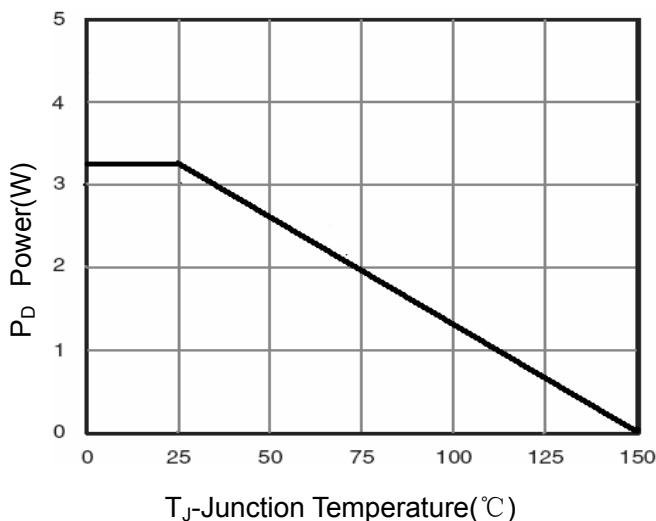


Figure 3 Power Dissipation

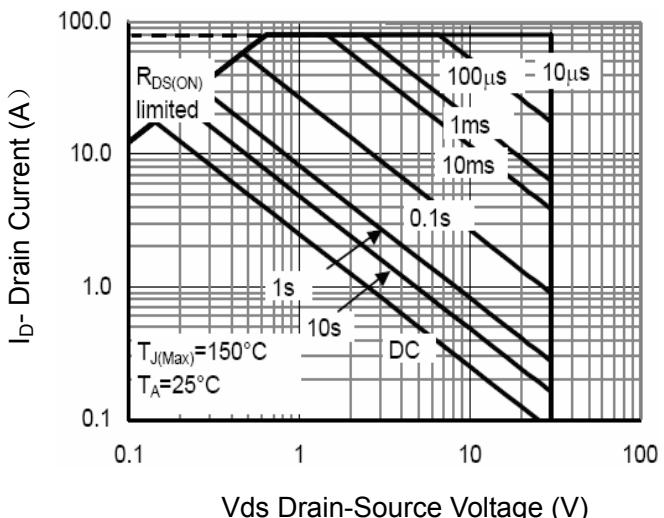


Figure 4 Safe Operation Area

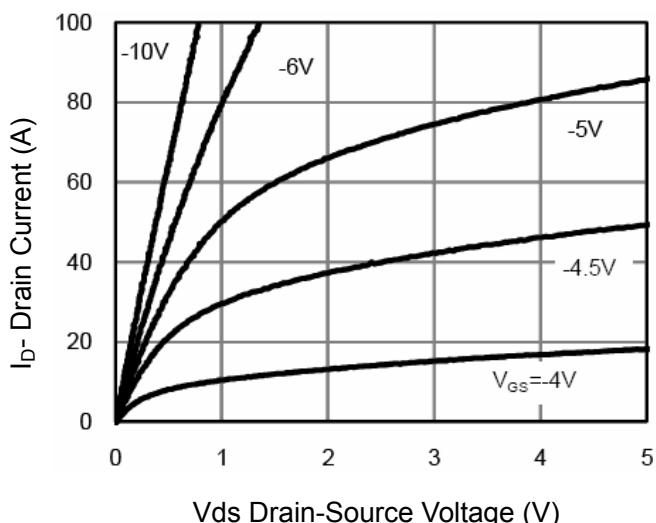


Figure 5 Output Characteristics

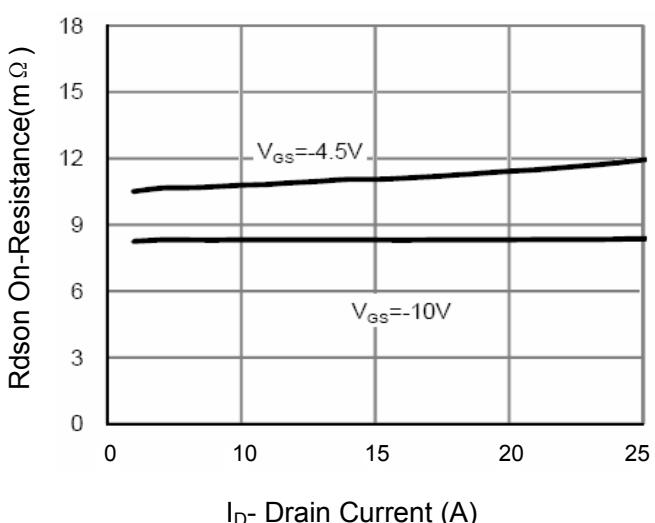


Figure 6 Drain-Source On-Resistance

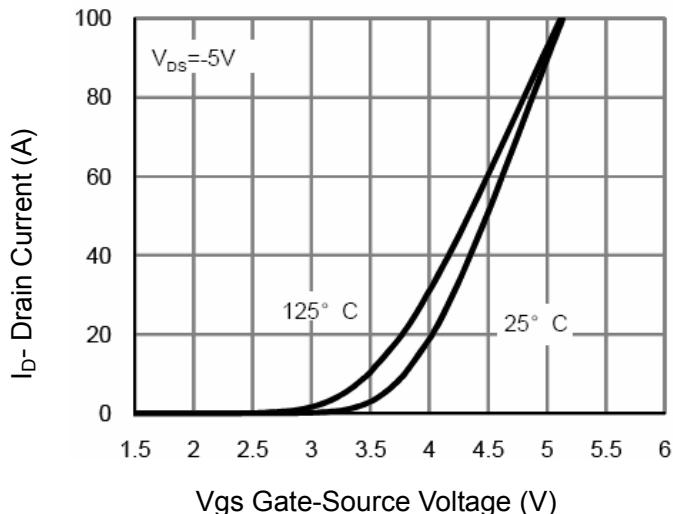


Figure 7 Transfer Characteristics

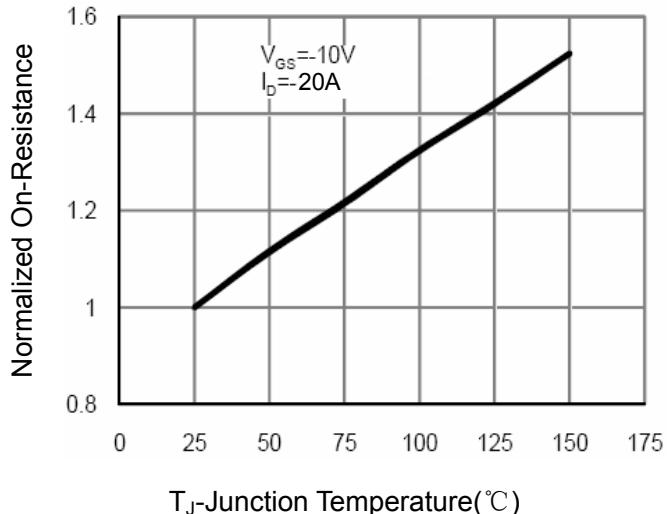


Figure 8 Drain-Source On-Resistance

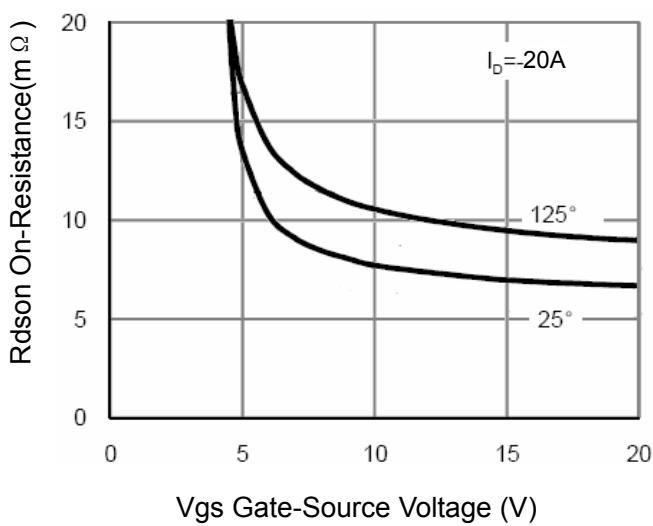


Figure 9 $R_{DS(on)}$ vs V_{GS}

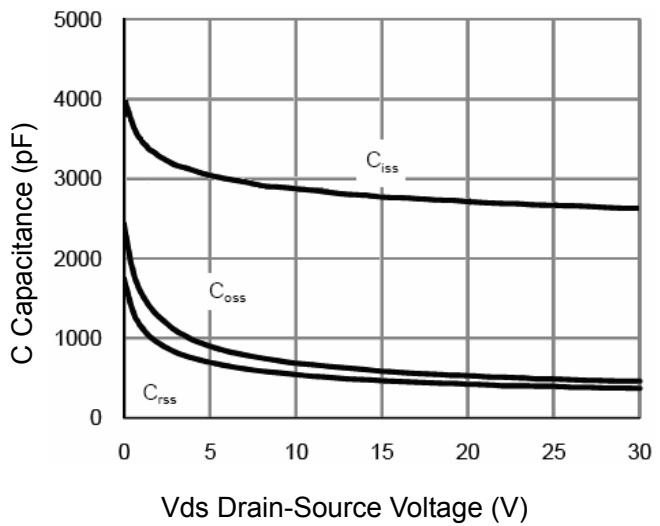


Figure 10 Capacitance vs V_{DS}

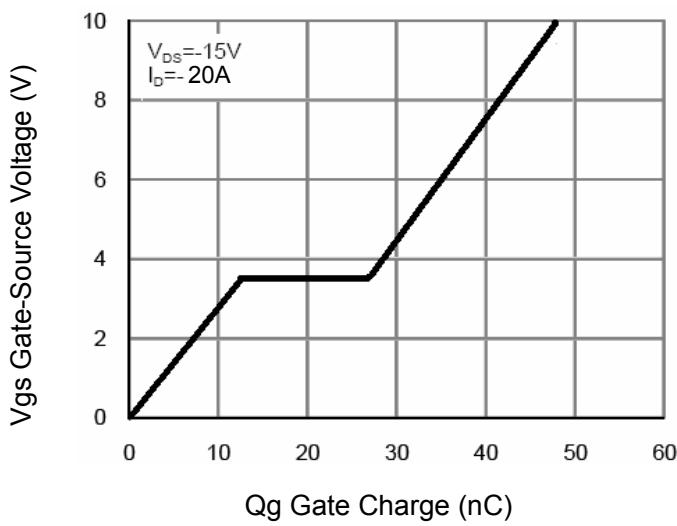


Figure 11 Gate Charge

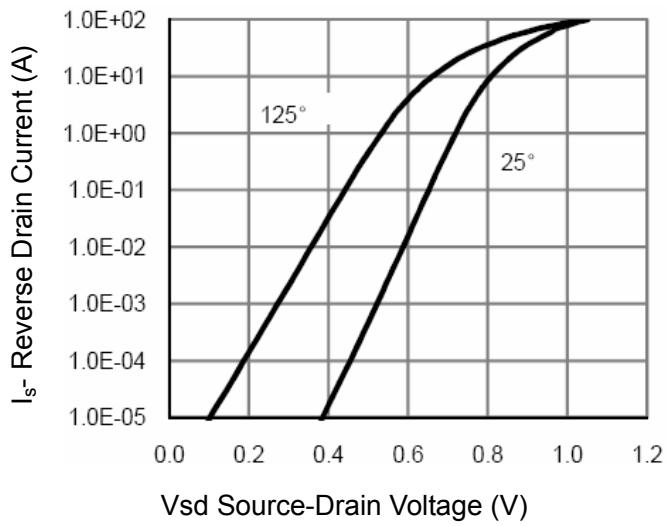


Figure 12 Source- Drain Diode Forward

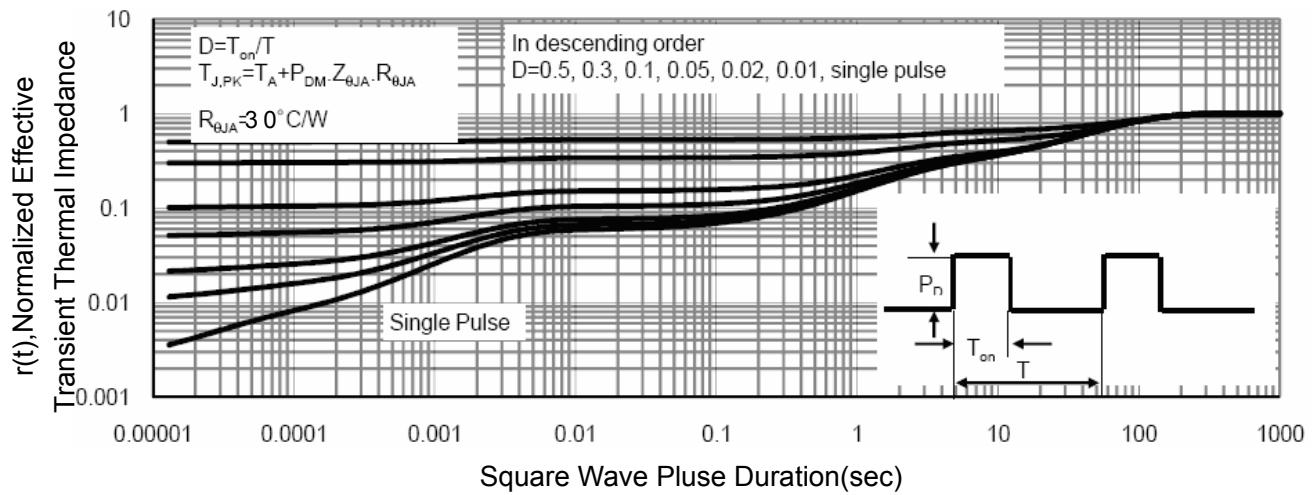
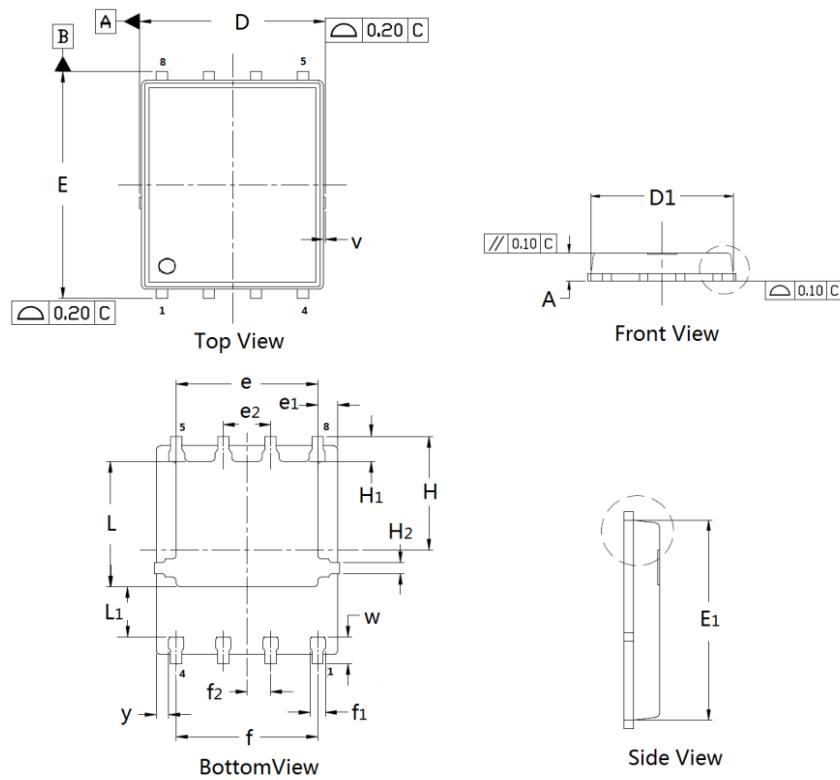


Figure 13 Normalized Maximum Transient Thermal Impedance

PDFN5×6 Package Outline Data

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.02	1.10	D	4.90	4.98	5.10
D ₁	4.80	4.89	5.00	E	6.00	6.11	6.20
E ₁	5.65	5.74	5.85	e	3.72	3.80	3.92
e ₁	--	0.54	--	e ₂	--	1.27	--
f	--	3.82	--	f ₁	0.31	0.37	0.51
f ₂	--	0.64	--	H	--	3.15	--
H ₁	0.59	0.63	0.79	H ₂	0.26	0.28	0.32
L	3.38	3.45	3.58	L ₁	--	1.39	--
V	--	0.13	--	w	0.64	0.68	0.84
y	--	0.34	--		--	--	--